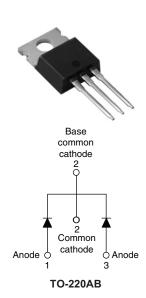


Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A



PRODUCT SUMMARY				
V _R	600 V			
V _F at 8 A at 25 °C	1.7 V			
I _{F(AV)}	2 x 8 A			
t _{rr} (typical)	18 ns			
T _J (maximum)	150 °C			
Q _{rr}	65 nC			
dI _{(rec)M} /dt	240 A/μs			

FEATURES

- · Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- · Lead (Pb)-free
- · Designed and qualified for industrial level

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

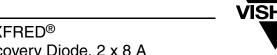
HFA16TA60C is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the HFA16TA60C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA16TA60C is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V_{R}		600	V	
Maximum continuous forward current per leg	- I _F	T _C = 100 °C	8		
per device			16	Α	
Single pulse forward current	I _{FSM}		60	A	
Maximum repetitive forward current	I _{FRM}		24		
Maximum navvar dissination	P _D	T _C = 25 °C	36	W	
Maximum power dissipation		T _C = 100 °C	14	VV	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

HFA16TA60CPbF

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s HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A

ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		600	-	-	
		I _F = 8 A		-	1.4	1.7	V
Maximum forward voltage V _{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1		
		I _F = 8 A, T _J = 125 °C		-	1.4	1.7	
Maximum reverse		$V_R = V_R$ rated	See fig. 2	-	0.3	5.0	
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See lig. 2	-	100	500	μΑ
Junction capacitance	C _T	V _R = 200 V	See fig. 3	=	10	25	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -		nΗ			

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	18	-	
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	37	55	ns
occ ng. o and ro	t _{rr2}	T _J = 125 °C		-	55	90	
Peak recovery current	I _{RRM1}	T _J = 25 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	3.5	5.0	А
See fig. 6	I _{RRM2}	T _J = 125 °C		-	4.5	8.0	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138	nC
See fig. 7	Q _{rr2}	T _J = 125 °C		-	124	360	110
Peak rate of fall recovery current during t _b	dI _{(rec)M} /dt1	T _J = 25 °C		-	240	-	A/μs
See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	210	-	Α/μδ

THERMAL - MECHANICAL SPECIFICATIONS PER LEG						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Junction to case, single leg conducting	Б		-	-	3.5	
Junction to case, both legs conducting	R _{thJC}		-	-	1.75	K/W
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- N/VV
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Maight			-	2.0	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220AB	HFA16TA60C			

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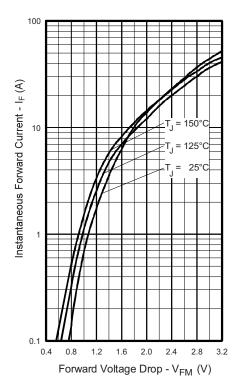


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

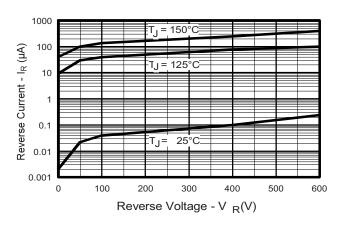


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

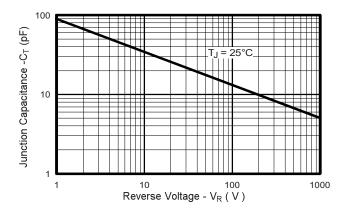


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

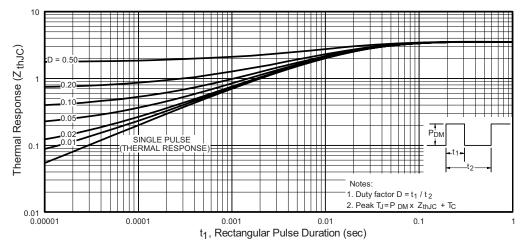


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

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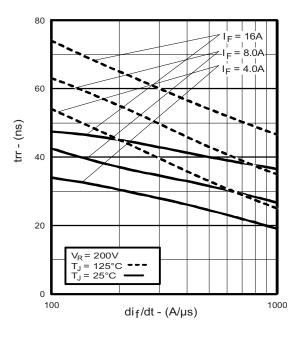


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

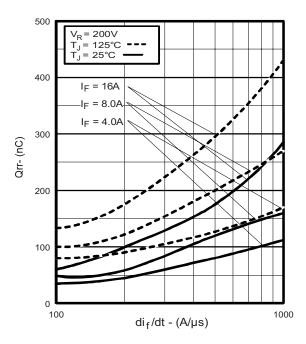


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

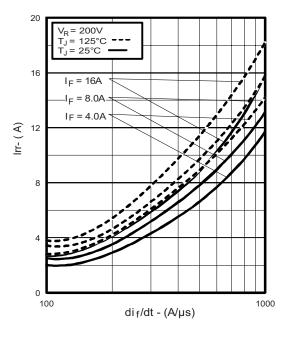


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

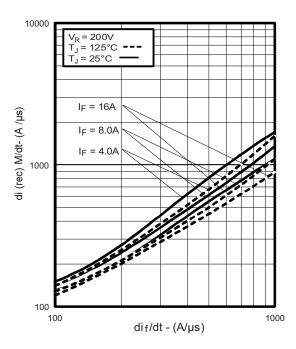


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)



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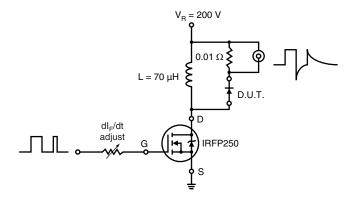
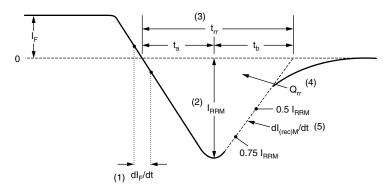


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- $\begin{array}{l} \text{(3) } \textbf{t}_{\text{rr}} \text{ reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going I}_{\text{F}} \text{ to point where a line passing} \\ \text{through 0.75 I}_{\text{RRM}} \text{ and 0.50 I}_{\text{RRM}} \\ \text{extrapolated to zero current.} \end{array}$
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95222				
Part marking information	http://www.vishay.com/doc?95225			



Vishay

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